

WHAT IS CLAIMED IS:

1. A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,
wherein said wafer includes an area in which crystal originated particles are generated,
wherein a surface density of particles having a particle size of not less than $0.12\text{ }\mu\text{m}$ on the wafer surface is not more than 15 counts/cm^2 , even after repeating the Standard Cleaning -1.
2. A silicon single crystal wafer for a particle monitor according to Claim 1, wherein said wafer has an oxygen concentration of not more than $13 \times 10^{17}\text{ atoms/cm}^3$ (old ASTM).
3. A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,
wherein said wafer includes an area in which crystal originated particles are generated, and further said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}\text{ atoms/cm}^3$,
wherein a surface density of particles having a particle size of not less than $0.12\text{ }\mu\text{m}$ on the wafer surface is not more than 1 count/cm^2 , even after repeating the Standard Cleaning -1.
4. A silicon single crystal wafer for a particle monitor according to Claim 3, wherein said wafer has an oxygen concentration of not more than $13 \times 10^{17}\text{ atoms/cm}^3$ (old ASTM).

5. A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 15 counts/cm², even after repeating the Standard Cleaning -1.

6. A silicon single crystal wafer for a particle monitor according to Claim 5, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm³ (old ASTM).

7. A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm³,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 1 count/cm², even after repeating the Standard Cleaning -1.

8. A silicon single crystal wafer for a particle monitor according to Claim 7,

wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm³ (old ASTM).

9. A silicon single crystal wafer for a particle monitor according to any one of Claim 1, 3, 5 or 7, wherein, in said Standard Cleaning - 1, the chemical component of the used solution is $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$, and the cleaning is repeated six times and each cleaning is carried out for 10 min.